Technical Data Datasheet 4287 REV. A

HERMETIC QUAD SILICON CARBIDE RECTIFIER

DESCRIPTION: FOUR 1200-VOLT, 5 AMP POWER SILICON CARBIDE RECTIFIERS IN A HERMETIC DUAL TO-257 PACKAGE. IDEAL FOR CONNECTION AS A BRIDGE.

FEATURES:

- NO RECOVERY TIME OR REVERSE RECOVERY LOSSES
- NO TEMPERATURE INFLUENCE ON SWITCHING BEHAVIOR
- CAN BE USED AS A SINGLE PHASE FULL WAVE BRIDGE BY EXTERNALLY CONNECTING TWO PINS

MAXIMUM RATINGS

ALL RATINGS ARE @ $T_C = 25$ °C UNLESS OTHERWISE SPECIFIED.

| RATING | SYMBOL | MAX. | UNITS |
|--|------------------|----------------|-------|
| PEAK INVERSE VOLTAGE | PIV | 1200 | Volts |
| MAXIMUM DC OUTPUT CURRENT (With $T_{\rm C}$ = 65 $^{\rm O}$ C) WHEN USED AS A BRIDGE | Io | 10 | Amps |
| MAXIMUM REPETITIVE FORWARD SURGE CURRENT (t = 8.3ms, Sine) per leg, $T_{\rm C}$ = 25 $^{\rm O}$ C | I _{FRM} | 30 | Amps |
| MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT (t = $10\mu s$, pulse) per leg, T_C = 25 $^{\circ}C$ | I _{FSM} | 100 | Amps |
| MAXIMUM POWER DISSIPATION, T _C = 25 °C | P _d | 30 | W |
| MAXIMUM THERMAL RESISTANCE, Junction to Case (Connected as a BRIDGE) | $R_{	heta JC}$ | 1.0 | °C/W |
| MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE* | Top, Tstg | -55 to +200 | °C |

^{*} Note: SiC semiconductors will handle at or above this operating and storage temperature. However, extended operational use of the packaged device above 175C may reduce its future performance. All qualification testing and screening per MIL-PRF-19500 will only be performed to 175C.

SENSITRON

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ELECTRICAL CHARACTERISTICS

| CHARACTERISTIC | TYP | MAX. | UNITS |
|---|------|------|-------|
| MAXIMUM FORWARD VOLTAGE DROP ($I_f = 5$ A PER LEG) V_f $T_J = 25$ °C | | 1.80 | |
| T _J =150 °C | 2.55 | 3.00 | Volts |
| MAXIMUM REVERSE CURRENT (1200V PIV PER LEG) I_r $T_J = 25$ °C | 0.05 | 0.20 | |
| T _J = 150 °C | 0.10 | 1.00 | mA |
| MAXIMUM JUNCTION CAPACITANCE (V _r =5V) per leg C _T | 450 | | pF |
| TOTAL CAPACITANCE CHARGE (V _R =1200V, I _F =5A, di/dt=500A/ μ s and T _J =25°C) Q _C per leg | 28 | N/A | nC |

Note: The following curves are for individual legs of the bridge.

Figure 1. Forward Characteristics

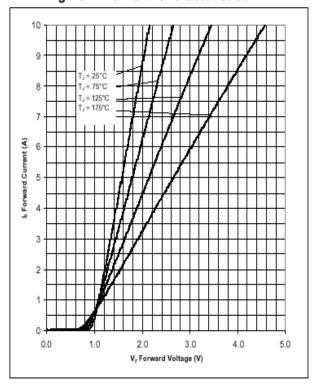
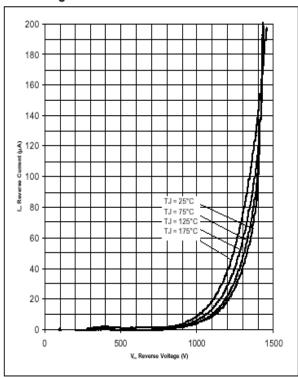


Figure 2. Reverse Characteristics

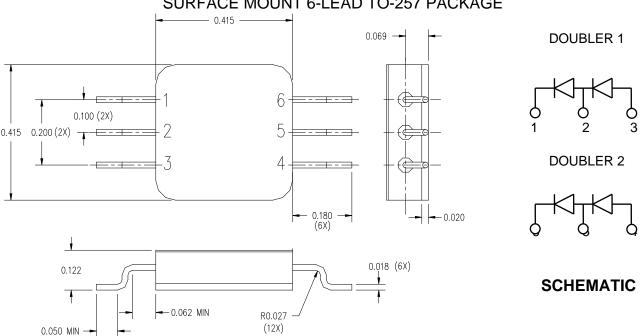


Application Note: Customers should be aware that at the current stage of technical development of SiC, the reverse avalanche capabilities of the device are limited.

Customer designs will need to accommodate these limitations and avoid exposure of the device to this and other potentially damaging conditions in their applications.

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MECHANICAL DIMENSIONS (inches) SURFACE MOUNT 6-LEAD TO-257 PACKAGE



 $TOLERANCE = .XXX \pm .010$

PINOUT TABLE

| TYPE | | PINS |
|----------------------------|---------------|------|
| DUAL RECTIFIER/DOUBLER (D) | CATHODE | 1 |
| | ANODE/CATHODE | 2 |
| | ANODE | 3 |
| | ANODE | 4 |
| | ANODE/CATHODE | 5 |
| | CATHODE | 6 |

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